

## 2SJ387 , 2SJ387

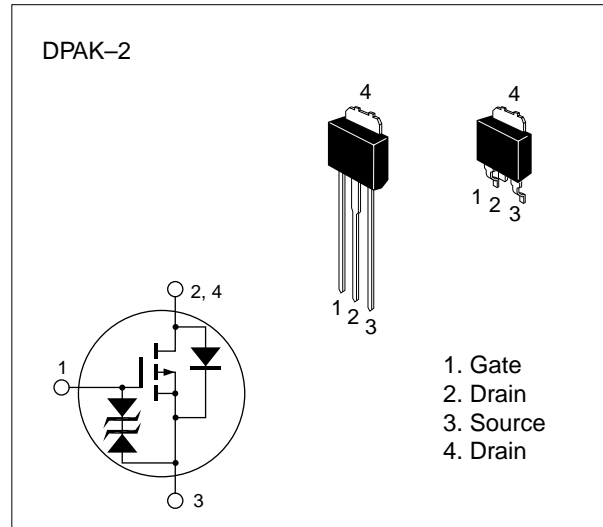
### Silicon P Channel MOS FET

#### Application

High speed power switching

#### Features

- Low on-resistance
- Low drive current
- 2.5 V Gate drive device can be driven from 3 V Source
- Suitable for Switching regulator, DC – DC converter



**Table 1 Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	-20	V
Gate to source voltage	V <sub>GSS</sub>	±10	V
Drain current	I <sub>D</sub>	-10	A
Drain peak current	I <sub>D(pulse)</sub> *	-40	A
Body-drain diode reverse drain current	I <sub>DR</sub>	-10	A
Channel dissipation	P <sub>ch</sub> **	20	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* PW ≤ 10 μs, duty cycle ≤ 1 %

\*\* Value at T<sub>c</sub> = 25°C

**Table 2 Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-20	—	—	V	$I_D = -10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±10	—	—	V	$I_G = \pm 200 \text{ } \mu\text{A}$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 6.5 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	-100	μA	$V_{DS} = -16 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.5	—	-1.5	V	$I_D = -1 \text{ mA}$ , $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.05	0.07	Ω	$I_D = -5 \text{ A}$ $V_{GS} = -4 \text{ V}^*$
		—	0.07	0.1	Ω	$I_D = -5 \text{ A}$ $V_{GS} = -2.5 \text{ V}^*$
Forward transfer admittance	$ y_{fs} $	7	12	—	S	$I_D = -5 \text{ A}$ $V_{DS} = -10 \text{ V}^*$
Input capacitance	$C_{iss}$	—	1170	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	$C_{oss}$	—	860	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	310	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$I_D = -5 \text{ A}$
Rise time	$t_r$	—	325	—	ns	$V_{GS} = -4 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	350	—	ns	$R_L = 2 \text{ } \Omega$
Fall time	$t_f$	—	425	—	ns	
Body-drain diode forward voltage	$V_{DF}$	—	-1.0	—	V	$I_F = -10 \text{ A}$ , $V_{GS} = 0$
Body-drain diode reverse recovery time	$t_{rr}$	—	240	—	μs	$I_F = -10 \text{ A}$ , $V_{GS} = 0$ , $di_F / dt = 20 \text{ A} / \mu\text{s}$

\* Pulse Test

